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SPECIAL SECTION ON THE 2015 BIPOLAR/BICMOS CIRCUITS AND TECHNOLOGY MEETING

Introduction to the Special Section on the 2015 Bipolar/BiCMOS Circuits and Technology Meeting	<i>J.-B. Begueret</i>	1963
<hr/>		
SPECIAL SECTION PAPERS		
Integration Trends in Monolithic Power ICs: Application and Technology Challenges	<i>M. Rose and H. J. Bergveld</i>	1965
A Wideband 20 to 28 GHz Signal Generator MMIC With 30.8 dBm Output Power Based on a Power Amplifier Cell With 31% PAE in SiGe	<i>B. Welp, K. Noujeim, and N. Pohl</i>	1975
Analog Circuit Blocks for 80-GHz Bandwidth Frequency-Interleaved, Linear, Large-Swing Front-Ends	<i>J. Hoffman, J.-R. Martin-Gosse, S. Shopov, J. J. Pekarik, R. Camillo-Castillo, V. Jain, D. Harame, and S. P. Voinigescu</i>	1985
Supply-Scaling for Efficiency Enhancement in Distributed Power Amplifiers	<i>K. Fang, C. S. Levy, and J. F. Buckwalter</i>	1994
Design Considerations for a 11.3 Gbit/s SiGe Bipolar Driver Array With a 5×6 V _{pp} Chip-to-Chip Bondwire Output to an MZM PIC	<i>H. Hettrich and M. Möller</i>	2006

SPECIAL SECTION ON THE 2015 COMPOUND SEMICONDUCTOR INTEGRATED CIRCUIT SYMPOSIUM

Introduction to the Special Section on the 2015 Compound Semiconductor Integrated Circuit Symposium	<i>S. Shahramian</i>	2015
<hr/>		
SPECIAL SECTION PAPERS		
A Novel 100 MHz–45 GHz Input-Termination-Less Distributed Amplifier Design With Low-Frequency Low-Noise and High Linearity Implemented With A 6 Inch 0.15 μ m GaN-SiC Wafer Process Technology	<i>K. W. Kobayashi, D. Denninghoff, and D. Miller</i>	2017
Multigate-Cell Stacked FET Design for Millimeter-Wave CMOS Power Amplifiers	<i>J. A. Jayamon, J. F. Buckwalter, and P. M. Asbeck</i>	2027

(Contents Continued on Back Cover)



55-nm SiGe BiCMOS Distributed Amplifier Topologies for Time-Interleaved 120-Gb/s Fiber-Optic Receivers and Transmitters	<i>J. Hoffman, S. Shopov, P. Chevalier, A. Cathelin, P. Schvan, and S. P. Voinigescu</i>	2040
A 234–261-GHz 55-nm SiGe BiCMOS Signal Source with 5.4–7.2 dBm Output Power, 1.3% DC-to-RF Efficiency, and 1-GHz Divided-Down Output	<i>S. Shopov, A. Balteanu, J. Hasch, P. Chevalier, A. Cathelin, and S. P. Voinigescu</i>	2054
A Highly Integrated 60 GHz 6-Channel Transceiver With Antenna in Package for Smart Sensing and Short-Range Communications	<i>I. Nasr, R. Jungmaier, A. Baheti, D. Noppeney, J. S. Bal, M. Wojnowski, E. Karagozler, H. Raja, J. Lien, I. Poupyrev, and S. Trotta</i>	2066
Capacitively-Coupled CMOS VCSEL Driver Circuits	<i>V. Kozlov and A. Chan Carusone</i>	2077
<hr/>		
REGULAR PAPERS		
A 2.4 GHz Interferer-Resilient Wake-Up Receiver Using A Dual-IF Multi-Stage N-Path Architecture	<i>C. Salazar, A. Cathelin, A. Kaiser, and J. Rabaey</i>	2091
A 110 nW Resistive Frequency Locked On-Chip Oscillator with 34.3 ppm/ $^{\circ}$ C Temperature Stability for System-on-Chip Designs	<i>M. Choi, T. Jang, S. Bang, Y. Shi, D. Blaauw, and D. Sylvester</i>	2106
A 5.6 nV/ $\sqrt{\text{Hz}}$ Chopper Operational Amplifier Achieving a 0.5 μV Maximum Offset Over Rail-to-Rail Input Range with Adaptive Clock Boosting Technique	<i>Y. Kusuda</i>	2119
A 25 Gb/s Hybrid-Integrated Silicon Photonic Source-Synchronous Receiver With Microring Wavelength Stabilization	<i>K. Yu, C. Li, H. Li, A. Titriku, A. Shafik, B. Wang, Z. Wang, R. Bai, C.-H. Chen, M. Fiorentino, P. Y. Chiang, and S. Palermo</i>	2129
A Fully Integrated Reconfigurable Switched-Capacitor DC-DC Converter With Four Stacked Output Channels for Voltage Stacking Applications	<i>T. Tong, S. K. Lee, X. Zhang, D. Brooks, and G.-Y. Wei</i>	2142
A 0.4W-to-21W Fast-Transient Global-Search-Algorithm Based Integrated Photovoltaic Energy Harvester With 99% GMPPPT Efficiency and 94% Power Efficiency	<i>S. Upadhyay and H. Lee</i>	2153
A 25.3 μW at 60 fps 240×160 Pixel Vision Sensor for Motion Capturing With In-Pixel Nonvolatile Analog Memory Using CAAC-IGZO FET	<i>T. Ohmaru, T. Nakagawa, S. Maeda, Y. Okamoto, M. Kozuma, S. Yoneda, H. Inoue, Y. Kurokawa, T. Ikeda, Y. Ieda, N. Yamade, H. Miyairi, M. Ikeda, and S. Yamazaki</i>	2168
A Sub-0.5 Electron Read Noise VGA Image Sensor in a Standard CMOS Process	<i>A. Boukhayma, A. Peizerat, and C. Enz</i>	2180
Ultra-Compact and Robust Physically Unclonable Function Based on Voltage-Compensated Proportional-to-Absolute-Temperature Voltage Generators	<i>J. Li and M. Seok</i>	2192